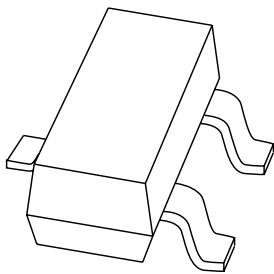


DATA SHEET



BCW31; BCW32; BCW33 NPN general purpose transistors

Product data sheet
Supersedes data of 2000 Jul 04

2004 Feb 06

NPN general purpose transistors

BCW31; BCW32; BCW33

FEATURES

- Low current (100 mA)
- Low voltage (32 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistors in a plastic SOT23 package.
PNP complements: BCW29 and BCW30.

MARKING

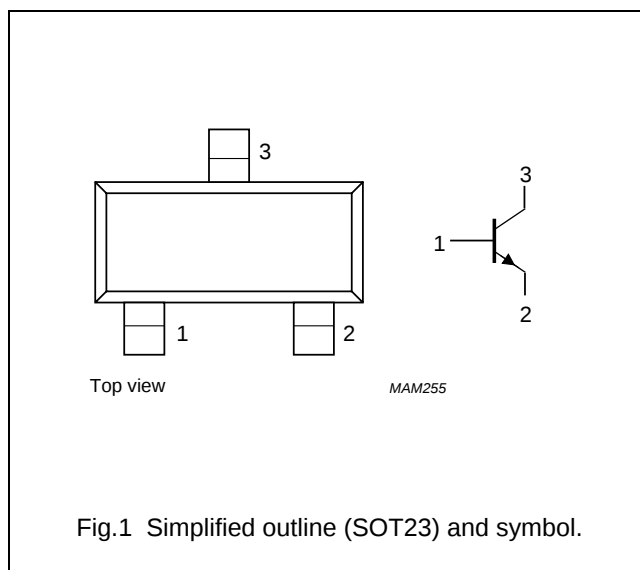
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW31	D1*
BCW32	D2*
BCW33	D3*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BCW31	–	plastic surface mounted package; 3 leads	SOT23
BCW32			
BCW33			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CB0}	collector-base voltage	open emitter	–	32	V
V_{CEO}	collector-emitter voltage	open base; $I_C = 2\text{ mA}$	–	32	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

NPN general purpose transistors

BCW31; BCW32; BCW33

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 32\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 32\text{ V}; T_j = 100\text{ °C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$				
	BCW31		–	190	–	
	BCW32		–	330	–	
	BCW33		–	600	–	
	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$				
	BCW31		110	–	220	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	120	250	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	210	–	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	750	–	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	850	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	550	–	700	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

NPN general purpose transistors

BCW31; BCW32; BCW33

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23

The diagrams illustrate the SOT23 package outline. The top view shows a rectangular body with a width dimension D and a lead spacing dimension e . The side view shows a height dimension A , a lead height dimension H_E , and a lead length dimension L_p . A detail view 'X' shows the lead profile with dimensions A_1 , Q , and c . The bottom view shows the lead positions 1, 2, and 3, with dimensions e_1 , b_p , and w . A scale bar indicates 0 to 2 mm.

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16